	Туре	L #	Hits	Search Text	DBs	Time Stamp
-	BRS	<u>-</u> 1	309	(memory and logic adj1 device\$1).ti.	DOMAC; DE; EPO; JPO; DERWEN T; IBM_TE	2002/03/31 16:56
0.	BRS	L2	29246	first nearl transistor and second adjl transistor	USPAT; US-PGP UB; EPO; JPO; LERWEN I;	2002/03/3.
.3	BRS	L3	5	1 and 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD	2002/03/31 16:47
	and		2. C I. (i	omomony nearl device\$land logic adjl device\$l/.ti.	USPAT; US-PGP TB; EPO; JEC; JERWEN T; IBM_TD B	. 6 6/19,181 16:45
f)	BRS	L5		(memory nearl device\$1 and logic adj1 device\$1).ti.	USPAT; US-PGP UB; EPO; JPO; DERWEN 1; IRM_TD	2002/03/31 16:58

	Туре	L #	Hits	Search Text	DBs	Time Stamp
8	BBS	7.6	9	5 and transistor	USPAT, US-PGH UB; EPO; JPO; DERWEN T; LEM TO	2002/03/31 :00:45
7	BRS	L7	3338	memory nearl device\$1 and logic adjl device\$1	DERWEN T; BM_TD B	2002/03/3. 16:57
-	BRE	Lø		dual adjī gate adjī ozide\$l	USPAT; US-PGP UB; EPO; CPO; CRAWEN T;	
	BRS	ĭ.9	16	7 and 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31
				t and transist :	UCPAT; TUP; ERU; TERMEN; TERMEN; B	

	Туре	L #	Hits	Search Text	DBs	Time Stamp
	888		39264	gate adfl oxide&!	USPAT; US-PGE UE; EPU; Thu; Thu;	>
12	BRS	L12	422	7 and 11	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:0€
	bks	Ll s	υg	vi tavilila (j. transistor	UMPAT; UM-PGP UB; UB; UBO; DERWEN T; IBM_TD B	
2.4		L14		13 and thickness	DERWEN T; SHM TL	2002/03/31 17:06
7.5	BRC	L15		14 and (oxidation or :xid\$3)	UB; EPO; JPO; DERWEN T; IBM_TD	2002/03/31 17:00

 	Туре	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	-	15 and (high adj1 temperature)	UPO; UPO; DERWEN T; IBM TO	2002/03/31 17:13
- 1	BRS	/	ō94	(dielectric adji layer) nearh (date adjl oxidosi)	USPAT; US-PGP UB; EPO; JPO; JEAWHHI	
10	BRS	L19	7	15 and 18	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:14
- u				V and IV	USPAT; US-PGP TB; EFO; TPO; LEFWEL T; IBM TL	. 0 27 - 1 31 T:le
20	EQS	1.20	93	((dielectric or silicom adj1 dioxide) adj1 layer) near5 (gate adj1 oxide\$1)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IHM_TO	2002/03/31 17:23

	Туре	L #	Hits	Search Text	DBs	Time Stamp
2.2	BRG	1.01		7 and 20	USPAT; US-PGF UB; EPO; UPO; UPO; URAMENT O; UBAC TO	0002/03/31 17:01
22	BRS	L22	28	21 and transistor	UCFAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:27
23	BRC		14305	advanced adjl miss - :d*1 devices	USPAT; US-PGP UE; EE; UPG; DERWEN T; IBM_TD B	
0.4	BRS	L24	193	7 and 23	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TL B	2002/03/31 17:23
				. 4 abo date adil omiqe€i	DATAT; FOR POR FRANCE REALITY	

	Туре	L #	Hits	Search Text	DBs	Time Stamp
V 6.	15 th C				USPAT; CU-FGF CA; EFFUE FFFUE FFFUE B	
0.73	BBS	- 27	3	4551910.pn.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; TBM TD	2002/03/31 17:43
		*			DERWEN BM_TD B	2002/12/31 17:43
2.9	5,5,0		14	7 and 28	USPAT; US-PGP UB; EPO; JPO; HEAMEN	1012/01, 31 17:
30	BRS	T.30	3	5057449.pn.	UMPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	002/03/31

	Туре	L #	Hits	Search Text	DBs	Time Stamp
					DERWELL BM_TE BM_TE B	:
32	BRS	L32	53	31 and 7	USPAT; US-PGE UB; EPO; JPO; DERWEN C; LBE II	2002/03/31
33	BRS	<u>1</u> 33	2	1 and (silicon adj1 nitride) near5 (oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	
AM				l and siling will Dings inward posts and William	USPAT; US-PGP UB; E:; ::; ::::; :::::::::::::::::::::::	· · · · · · · · · · · · · · · · · · ·
11.			Ć [1		USPAT; US-PGP UB; EPO; JPO; DERWEN T;	2002/93/31 18:50

	Туре	L #	Hits	Search Text	DBs	Time Stamp
36	BRS	2.37	17	7 and (silicon adj1 nitride) near5 (boron or oxidized)	USPAT; US-PGI UB; EPO; JPO; DERWEN T; IBM_TI	2002/03/31 18:51
	land.		12 T	Statistical Control (1985) Geography (1986) Klatistic	UMPAT; UMPEGF HE; HE; HEFMEN TY; LEM_TO B	i Vitoria Vitoria
3.3	BRS	138	41	7 and (silicon adj1 nitride) near3 (oxidized or oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TD	2002/03/31 19:26
39	BRS	1.39	15	7 and rediffer out to	UPPAT; UPPOP UE; EPO; DERWEN T; IBM TD B	2002/03/31 19:29
	EBS	7,40	•	7 and (silicon adj1 dioxide) near? (oxidiced or oxidation	USPAT; US-PGP UB; EPO; JPO; IEFMENT I;	C4.2 * 1 + 1

	Туре	L #	Hits	Search Text	DBs	Time Stamp
41	BRS	L41	33	<pre>/ and (gate adjl oxide) near3 (oxidized or oxidation)</pre>	USPAT; US-PGS UB; EPO; JPO; DEPWENT; LHM_TO	
78.22	BRU	i d'al	14	41 and (high near) temperature)	US-FGE UB; EPO; JPO; DERWEN T; IBM_TO	2002/03/3: 20:05
	BBS		1.5.1	7 and (pxide\$1 or dicxide) neart (xidation or cxidined)	USPAT; US-PGP UB; EPC; OBERWEN 1; 18M TO B	
44	BRS	L44	75	43 and (high adj1 temperature)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TD	2002/03/31 20:06
.; c.	EEC	1.45	£9		TAMEAT; TIMESHAT; TIME; TIME; TIMESHAME TIMESH	